

METHOD FOR PRODUCING A GATE STRUCTURE FOR A MOS TRANSISTOR

ABSTRACT

5 In a method for producing a gate structure for a MOS transistor, first, a layer sequence of oxide layer, auxiliary layer and masking layer is generated on a substrate, wherein the auxiliary layer and the masking layer are patterned to determine an edge separating an area of the oxide layer
10 covered by these layers from an exposed area thereof. Afterwards, an oxidation is performed to generate an oxide ramp in the area of the edge. Then, the auxiliary layer is partly removed to generate a hollow space of predetermined length between the oxide layer and the masking layer. A gate
15 electrode material is introduced into the hollow space for generating a gate electrode.